

a capacitor comprising an electrode having a titanium nitride layer provided beneath a platinum-rhodium layer and a platinum layer on top of the platinum-rhodium layer; and

a conductive plug providing electrical contact between the source/drain region and the lateral surface of the electrode.

Please add new claim 126.

126. (new) A memory cell, comprising:

a substrate;

a transistor including a gate on said substrate and a source/drain region in said substrate disposed adjacent to said gate;

a capacitor comprising an electrode having a layer comprising platinum-rhodium material and at least one layer comprising platinum material on top of the platinum-rhodium layer, said platinum-rhodium layer comprises approximately more than 20 percent rhodium, wherein the electrode has a lateral surface aligned with the source/drain region; and

a conductive plug providing electrical contact between the source/drain region and the lateral surface of the electrode.